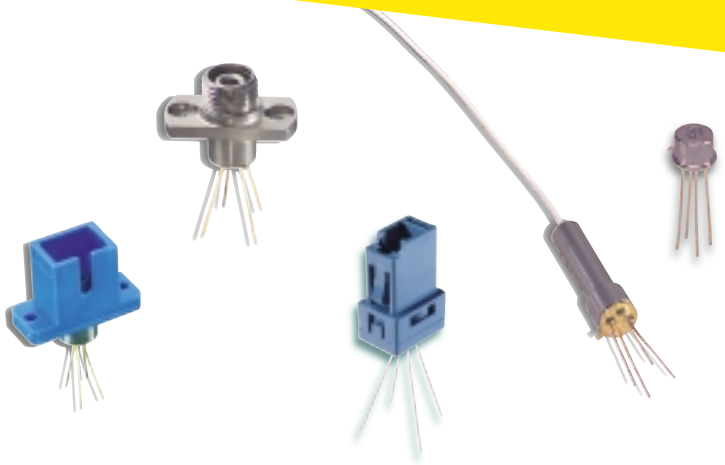
JDS Uniphase

Product Bulletin



EDR 51xx Series
Access PIN-TIA Receivers for 155 Mb/s and 622 Mb/s

(EDR 512x) Specifications

Conditions (unless noted): V_{CC} = +5V, T_A = 25°C, R_L = 50Ω (AC coupled), λ = 1300 nm

All specifications without connector.

Model	EDR 512B			EDR 512C			EDR 512D			
Parameter	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Units**
Gain[1]	15	20		15	20		25	35		V/mW
Bandwidth	110	200		110	200		110	200		MHz
Sensitivity[2]		-38.0	-36.0		-38.0	-36.0		-38.5	-36.5	dBm
Overload	0	2		0	2		0	2		dBm
Output Resistance		70			70			70		Ω
Maximum Output Voltage		400			400			800		$mV_{pk\text{-}pk}$
AGC Time Constant		4000			4000			4000		µs
AGC Threshold		2			2			2		µW

1. Measured at 100 MHz.
2. BER of 1E-10, 120 MHz noise filter.

(EDR 515x) Specifications

Conditions (unless noted): V_{CC} = +3.3V, T_A = 25°C, R_L = 50Ω (AC coupled), λ = 1300 nm

All specifications without connector.

Model	EDR 515B			EDR 515C			EDR 515D			
Parameter	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Units**
Gain[1]	1.7	2.2		1.7	2.2		3.0	4.0		V/mW
Bandwidth	415	500		415	500		415	500		MHz
Sensitivity[2]		-31.5	-30.0		-31.5	-30.0		-32.5	-31.0	dBm
Overload	-7.0	-4.0		-7.0	-4.0		-7.0	-4.0		dBm
Output Resistance	45	60	75	45	60	75	45	60	75	Ω
Maximum Output Voltage			500			500			950	$mV_{pk\text{-}pk}$

1. Measured at 300 MHz.
2. BER of 1E-10, 415 MHz noise filter.

Key Features

Electro-optical

- InGaAs PIN photodiode with silicon transimpedance amplifier
- Operate on single supply
  EDR 512x (5V)
  EDR 515x (3.3V or 5V)
- Three standard pin-out configurations
  EDR 51xB - single-ended output
  EDR 51xC - single-ended output with photodiode access
  EDR 51xD - differential output
- Cost effective in receiver designs where sensitivity is limited by the post-amplifier
- Shielded pre-amplifier makes it immune to crosstalk with transmitter or to other EMI
- -40 to +85°C operating range

Packaging

- Integrated 4-pin coaxial package
- Connector receptacle (panel or PCB mount) and fiber pigtailed versions
- Case grounded versions

Applications

- Single mode 155 Mb/s (EDR 512x) and 622 Mb/s (EDR 515x) ATM receivers
- Campus network backbone
  - Add/drop multiplexers
  - Digital loop carriers
  - Digital crossconnects
  - Optical networking
- Enterprise network backbone

Description

The EDR 51xx Series incorporates a 75 µm InGaAs PIN photodetector coupled with a low cost BiCMOS transimpedance amplifier (TIA) designed to operate at 155 Mb/s (EDR 512x) or 622 Mb/s (EDR 515x). The PIN transduces optical power into current with high efficiency. The TIA converts the current signal into a voltage signal with a very low input noise current contribution. The EDR 512x TIA also integrates an automatic gain control (AGC) circuit which decreases the light to voltage conversion factor when the average incident optical power is relatively high.

The EDR 51xx Series are assembled in rugged coaxial packages. They are available with a connector receptacle or as a single mode fiber pigtail. Standard choices for connector receptacles are LC, SC and FC. In addition, the EDR 51xx Series are available in several standard pin-out configurations. The EDR 51xB is the simplest configuration and provides a single ended output. The EDR 51xC provides access to the photodiode current for those customers who need to design an alarm circuit. The EDR 51xD provides a differential output for higher gain performance without sacrifice to sensitivity and bandwidth.

Performance Highlights

The EDR 51x Series offer a sensitivity of better than -36 dBm (EDR 512x) or -30 dBm (EDR 515x) with appropriate filtering and a minimum overload of 0 dBm (EDR 512x) or -7 dBm (EDR 515x). This large dynamic range makes these products ideal for both long and short range applications. A time constant of 4 milliseconds makes the AGC circuit of the EDR 512x models very stable, even during reception of the longest streams of high or low logic levels. The EDR 51x Series operate over -40 to +85°C.

The EDR 51x Series provide significant benefits over hybrid designs and 14-pin receivers. Integration of the TIA with the PIN detector onto the TO-46 header reduces parasitic capacitances and lead inductances. The TO-52 cap hermetically seals the hybrid and provides EMI shielding especially from the transmitter circuit. These advantages improve sensitivity over designs that place the amplifier outside the capsule and away from the detector. The EDR 51x Series, which have four pins, are advantageous over 14-pin receivers because they require less board space and fewer electrical connections. In addition, the EDR 51xx Series operate from a single power supply, even in the pin-out configuration which provides photodiode current monitoring. The smaller form factor and the need for a single power supply make the EDR 51x Series a less expensive, high performance alternative to other kinds of optical receivers.

Typical Applications

The EDR 51xx Series are designed for many applications, including single mode 155 Mb/s (EDR 512x) and 622 Mb/s (EDR 515x) ATM receivers. The EDR 51xx Series exceed Long Reach OC-3 (EDR 512x) and OC-12 (EDR 515x) SONET receiver specifications and are ideal for transceiver designs or board level discrete designs. Applications include receivers for digital cross connects, digital loop carriers, add/drop multiplexers, optical network units and switches and routers for LAN and WAN backbones.

External Circuitry

When designing the EDR 51xx Series into an optical receiver, standard high speed printed circuit board design practices should be observed. For example, bypassing of the power supply is recommended so as to reduce noise that appears at the output of the PIN-TIA.

If signal traces are relatively long, use impedance matching techniques to maximize power transfer from the PIN-TIA to its load: for microstrip design, assume 70 ohms (EDR 512x) and 60 ohms (EDR 515x) as the output impedance for the PIN-TIA. Note as well that the output of the PIN-TIA is DC-coupled. Since most applications require AC-coupled stages, a high-Q RF chip capacitor should be placed on the output of the module. To eliminate oscillations, the PIN-TIA should be mounted on a circuit board with a large, low impedance ground plane. All the PIN-TIA leads should be made as short as possible in order to reduce excess inductances. As a general rule, receiver bandwidth requirements need only be greater than about 1/3 of the bit rate at which they are intended to operate. A receiver for a 155 Mb/s system must have a bandwidth greater than 110 MHz. A receiver for a 622 Mb/s system must have a bandwidth greater than 415 MHz. On the other hand, any frequency component above 110 MHz for 155 Mb/s systems or above 415 MHz for a 622 Mb/s systems contributes excess noise to the output. The excess noise needlessly reduces the sensitivity of the receiver. The receiver designer may therefore improve the PIN-TIA sensitivity by placing a low pass noise filter on the output.

EDR 512x
DC Electrical Characteristics and Maximum Ratings

Parameter	Min	Typ	Max	Units
Supply Voltage (V_{CC})	4.5	5.0	5.5	V
Output Offset Voltage	2.9	3.2	3.5	V
Diff. Output Offset Voltage[1]		80		mV
Supply Current (I_{CC})		25	50	mA
Dark Current[2]			1	nA
Optical Input Power			5.0	mW
Operating Temperature	-40		85	°C
Storage Temperature	-40		85	°C
Photodiode Voltage (V_{pd})[2]	2		25	V

1. Applies to EDR 512D only.
2. Applies to EDR 512C only.

EDR 515x
DC Electrical Characteristics and Maximum Ratings

Parameter	Min	Typ	Max	Units
Supply Voltage (V_{CC})	3.0	3.3/5.0	5.25	V
Output Offset Voltage		2.0/3.7		V
Diff. Output Offset Voltage[3]		7.0		mV
Supply Current (I_{CC})	12	25/35	50	mA
Dark Current[4]			1.0	nA
Optical Input Power			5.0	mW
Operating Temperature	-40		85	°C
Storage Temperature	-40		85	°C
Photodiode Voltage (V_{pd})[4]	2		25	V

3. Applies to EDR 515D only.
4. Applies to EDR 515C only.

Ordering Information

Product Number	Description
EDR 51xB	PIN-TIA with single ended output and case connected to ground pin
EDR 51xC	PIN-TIA with access to photodiode current and case connected to ground pin
EDR 51xD	PIN-TIA with differential output voltage

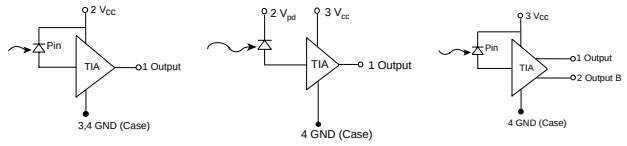
Note: EDR 51xx Series can be ordered in the following packaging options by adding the appropriate suffix to the base product number as shown below.

EDR 51xx TL	Transistor outline with lensed cap
EDR 51xx FJS	Single mode (900 µm) fiber jacket
EDR 51xx RLC	LC receptacle with 2-hole flange
EDR 51xx RFC2	FC receptacle with 2-hole flange
EDR 51xx RSC-DM	SC receptacle, dual-mount (panel & board)
EDR 51xx RSC-FM	SC receptacle, front-mount (panel only)

Note: EDR 51xx FJS packages can be ordered with the following pigtail connector options by adding the appropriate suffix to the base product number as shown below.

EDR 51xx FJS FC/SPC	900 µm buffer with FC/SPC connector
EPM 51xx FJS SC/SPC	900 µm buffer with SC/SPC connector
EPM 51xx FJS LC	900 µm buffer with LC connector

Electrical Schematics



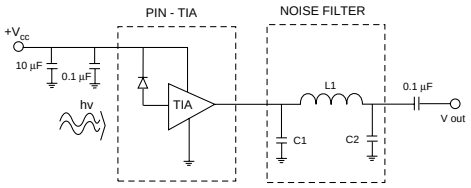
Access to photodiode current is provided.

Differential output is provided.

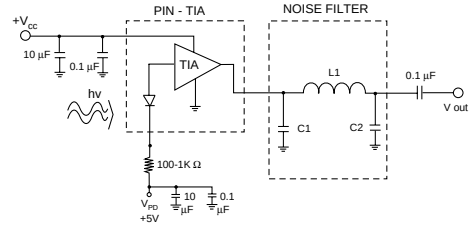
EDR 512B EDR 515B | **EDR 512C EDR 515C** | **EDR 512D EDR 515D**

Typical Low Pass Noise Filter Design for 155 Mb/s and 622 Mb/s

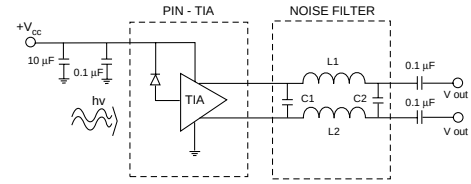
EDR 512B EDR 515B



EDR 512C EDR 515C



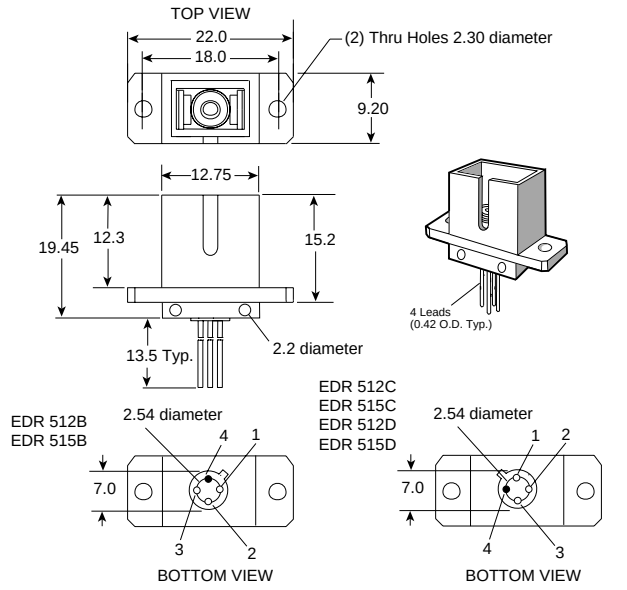
EDR 512D EDR 515D



	L1	L2	C1	C2
EDR 512B	150 nH	-	27 pF	27 pF
EDR 512C	150 nH	-	27 pF	27 pF
EDR 512D	120 nH	120 nH	18 pF	18 pF
EDR 515B	33 nH	-	10 pF	10 pF
EDR 515C	33 nH	-	10 pF	10 pF
EDR 515D	30 nH	30 nH	5.6 pF	5.6 pF

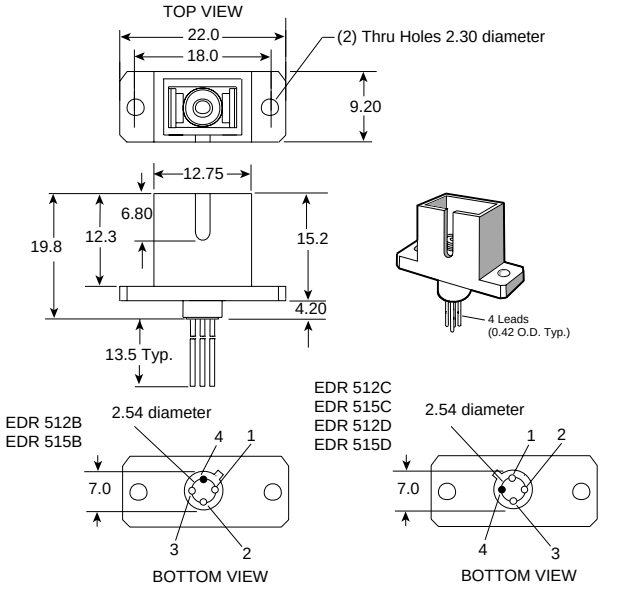
Mechanical Dimensions - All dimensions in mm (nominal)

EDR 51xx RSC-DM



Note: Critical dimensions meet NTT specifications.
Other dimensions subject to revision.

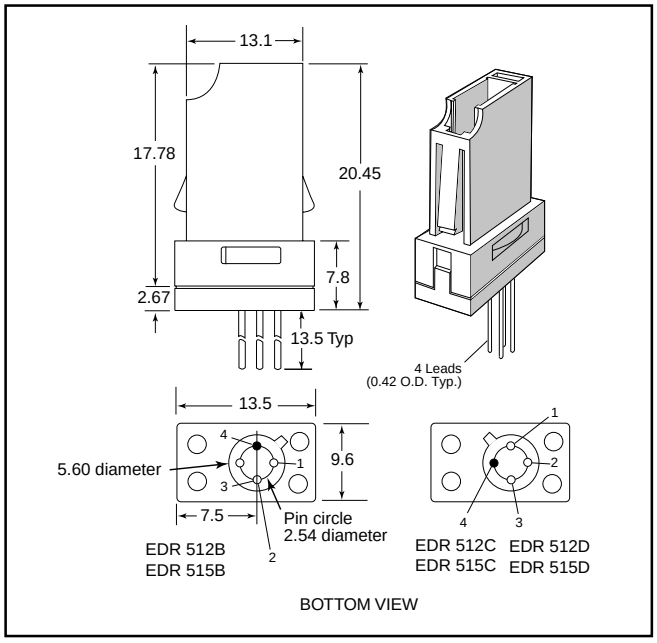
EDR 51xx RSC-FM



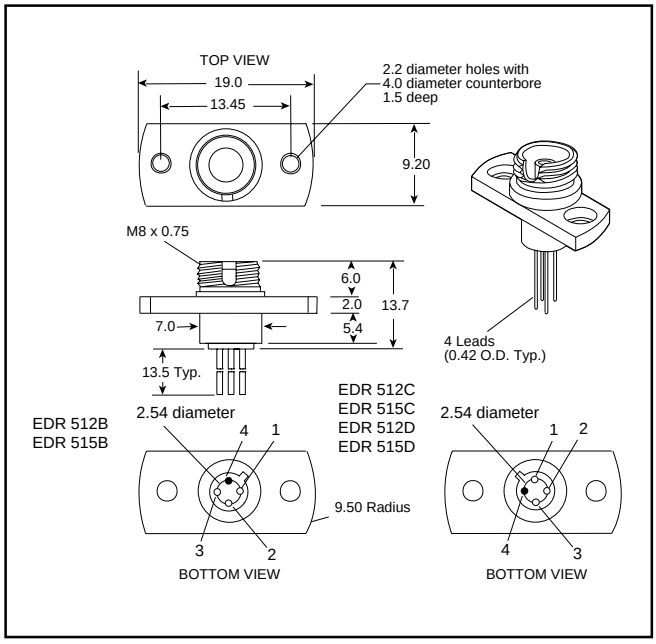
Note: Critical dimensions meet NTT specifications.
Other dimensions subject to revision.

Mechanical Dimensions - All dimensions in mm (nominal)

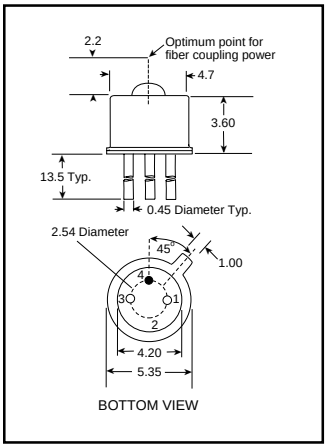
EDR 51xx RLC



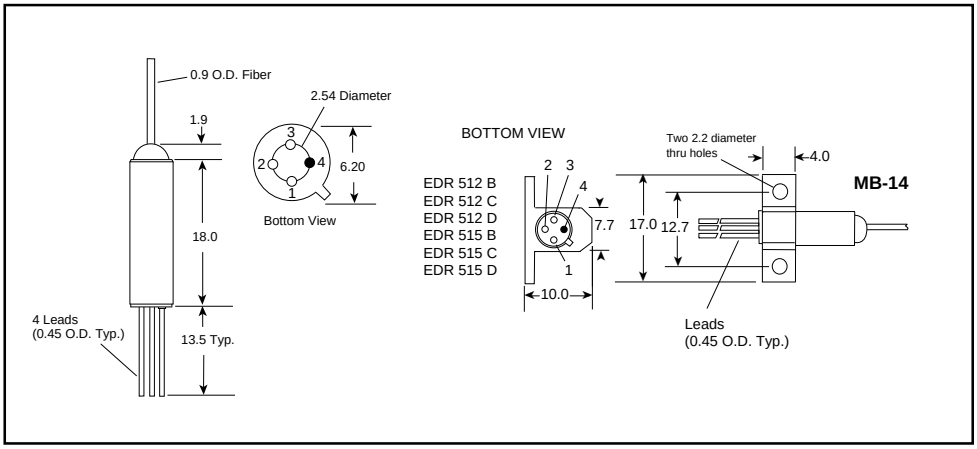
EDR 51xx RFC2



EDR 51xx TL



EDR 51xx FJS w/ Bracket Option



Precautions for Use

ESD protection is imperative. Use of grounding straps, anti-static mats, and other standard ESD protective equipment is required when handling or testing an InGaAs PIN or any other junction photodiode. Fiber pigtails should be handled with less than 10 N pull and with bending radius greater than 1". Soldering temperature of the leads should not exceed 260 °C for more than 10 seconds.

Quality Vision

We have a leadership position in the optoelectronic industry with a vision for excellence in quality. The company is committed to providing customers with the highest levels of quality and reliability in design and manufacturing. The top priorities remain continuous process improvement and total customer satisfaction. We obtained ISO 9001 certification in 1996. In addition, the company maintains a strict quality control program to ensure that all products meet or surpass customer requirements.

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